

In re: Chung et al.  
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**In the Claims:**

1.-16. (Canceled)

17. (Original) A method of fabricating a capacitor of a semiconductor device, the method comprising:

forming a capacitor lower electrode on a semiconductor substrate;

forming a dielectric layer on the lower electrode; and

sequentially stacking a metallic layer and an  $\text{Si}_{1-x}\text{Ge}_x$  layer on the dielectric layer to form an upper electrode comprising the metallic layer and the  $\text{Si}_{1-x}\text{Ge}_x$  layer.

18. (Original) The method of Claim 17 wherein the  $\text{Si}_{1-x}\text{Ge}_x$  layer comprises a doped  $\text{polySi}_{1-x}\text{Ge}_x$  layer.

19. (Original) The method of Claim 18, wherein the doped  $\text{polySi}_{1-x}\text{Ge}_x$  layer is formed by doping a  $\text{polySi}_{1-x}\text{Ge}_x$  layer with P or As.

20. (Original) The method of Claim 18, wherein the doped  $\text{polySi}_{1-x}\text{Ge}_x$  layer is formed by doping a  $\text{polySi}_{1-x}\text{Ge}_x$  layer with B.

21. (Original) The method of Claim 18, wherein the doped  $\text{polySi}_{1-x}\text{Ge}_x$  layer is formed by depositing a  $\text{polySi}_{1-x}\text{Ge}_x$  layer while simultaneously doping impurities.

22. (Original) The method of Claim 18, wherein the doped  $\text{polySi}_{1-x}\text{Ge}_x$  layer is deposited and simultaneously activated.

23. (Original) The method of Claim 22, wherein the  $\text{Si}_{1-x}\text{Ge}_x$  is deposited and simultaneously activated between about  $350^\circ\text{C}$  and about  $550^\circ\text{C}$ .

24. (Original) The method of Claim 18, wherein the doped  $\text{polySi}_{1-x}\text{Ge}_x$  layer is deposited and then activation and thermal treatment is performed.

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25. (Original) The method of Claim 24, wherein activation and thermal treatment is performed between about 400°C and about 550°C.

26. (Original) The method of Claim 17, wherein the metallic layer of the upper electrode comprises TiN, WN, TaN, Cu, W, Al, noble metals, oxide of the noble metals, and/or combinations thereof.

27. (Original) The method of Claim 17, wherein the doped polySi<sub>1-x</sub>Ge<sub>x</sub> layer is formed using low pressure chemical vapor deposition (LP CVD) using furnace type equipment, single wafer type equipment, and/or mini-batch equipment.

28. (Original) The method of Claim 17, wherein the lower electrode comprises a metallic layer.

29. (Original) A method of fabricating a capacitor of a semiconductor device, the method comprising:

forming a capacitor lower electrode on a semiconductor substrate;  
forming a dielectric layer on the lower electrode; and  
forming an Si<sub>1-x</sub>Ge<sub>x</sub> layer on the dielectric layer at about 550°C or less.

30. (Original) A method according to Claim 29, further comprising:  
thermally treating the Si<sub>1-x</sub>Ge<sub>x</sub> layer at about 550°C or less.